Abstracts

Comparison of Thermal-Shunt and Flip-Chip HBT Thermal Impedances: Comment on "Novel HBT with Reduced Thermal Impedance" (Comments)

T. Jenkins, C. Bozada, R. Dettmer, J. Sewell, D. Via, J. Barrette, J. Ebel, G. DeSalvo, C. Havasy, L. Liou, T. Quach, J. Gillespie, C. Pettiford, C. Ito, K. Nakano and R. Anholt. "Comparison of Thermal-Shunt and Flip-Chip HBT Thermal Impedances: Comment on "Novel HBT with Reduced Thermal Impedance" (Comments)." 1996 Microwave and Guided Wave Letters 6.7 (Jul. 1996 [MGWL]): 268-269.

As indicated in the above letter, reducing thermal impedance is a key to increasing heterojunction bipolar transistor (HBT) power densities. Also, as indicated by the above letter and others, several competing technologies are evolving to reduce the thermal impedance of HBT's. This comment specifically addresses the question: Does the flip-chip technology proposed in the above letter offer significantly lower HBT thermal impedance than the thermal-shunt technology?

❑ Return to main document.